

### FEATURES

- Very low supply current: 13  $\mu$ A**
- Low offset voltage: 15  $\mu$ V maximum**
- Offset voltage drift: 20 nV/ $^{\circ}$ C**
- Single-supply operation: 1.8 V to 5.5 V**
- High PSRR: 110 dB minimum**
- High CMRR: 110 dB minimum**
- Rail-to-rail input and output**
- Unity gain stable**
- Extended industrial temperature range**

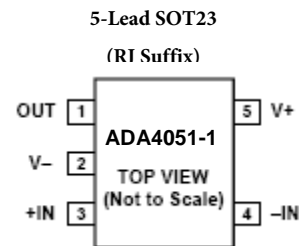
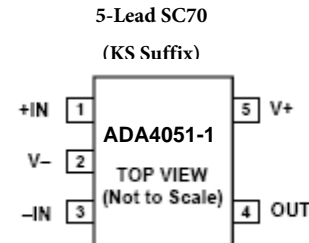
### APPLICATIONS

- Pressure and position sensors**
- Temperature measurements**
- Electronic scales**
- Medical instrumentation**
- Battery-powered equipment**
- Handheld test equipment**

### GENERAL DESCRIPTION

The ADA4051-1 is a single CMOS, micropower, zero-drift operational amplifier utilizing an innovative chopping technique. This amplifier features rail-to-rail input and output swing and extremely low offset voltage while operating from a 1.8 V to 5.5 V power supply. This amplifier also offers high PSRR and CMRR, while operating with a supply current of only 13  $\mu$ A per amplifier. This combination of features makes the ADA4051-1 amplifier an ideal choice for battery-powered applications where high precision as well as low power consumption is important. The ADA4051-1 is specified for the extended industrial temperature range of  $-40^{\circ}$ C to  $+125^{\circ}$ C. The ADA4051-1 amplifier is available in the standard 5-pin SOT23 and 5-pin SC70.

### PIN CONFIGURATION



The ADA4051-1 is a member of a growing series of zero-drift op amps offered by Analog Devices, Inc. Refer to Table 1 for a list of these devices.

Table 1. Op Amps

Supple	Micro Power, 5V	Low Power, 5V	5V	16V
Single		AD8538	AD8628	AD8638
Dual	ADA4051-2	AD8539	AD8629	AD8639
Quad			AD8630	

#### Rev. PrA

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## SPECIFICATIONS

## ELECTRICAL CHARACTERISTICS—5 V OPERATION

$V_{SY} = 5.0 \text{ V}$ ,  $V_{CM} = V_{SY}/2 \text{ V}$ ,  $T_A = 25^\circ\text{C}$ , unless otherwise noted.

Table 2.

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
INPUT CHARACTERISTICS						
Offset Voltage	$V_{OS}$	$0 \text{ V} \leq V_{CM} \leq 5 \text{ V}$		2	15	$\mu\text{V}$
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		0.02	0.1	$\mu\text{V}/^\circ\text{C}$
Input Bias Current	$I_B$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		20	70	$\text{pA}$
Input Offset Current	$I_{OS}$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			200	$\text{pA}$
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		40	100	$\text{pA}$
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			150	$\text{pA}$
Input Voltage Range		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	0		5	$\text{V}$
Common-Mode Rejection Ratio	CMRR	$0 \text{ V} \leq V_{CM} \leq 5 \text{ V}$	110	135		$\text{dB}$
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	106			$\text{dB}$
Large-Signal Voltage Gain	$A_{VO}$	$R_L = 10 \text{ k}\Omega$ , $0.1 \text{ V} \leq V_{OUT} \leq V_{SY} - 0.1 \text{ V}$	115	135		$\text{dB}$
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	106			$\text{dB}$
Input Resistance	$R_{IN}$			8		$\text{M}\Omega$
Input Capacitance, Differential Mode	$C_{INDM}$			2		$\text{pF}$
Input Capacitance, Common Mode	$C_{INCM}$			5		$\text{pF}$
OUTPUT CHARACTERISTICS						
Output Voltage High	$V_{OH}$	$R_L = 10 \text{ k}\Omega$ to $V_{CM}$	4.96	4.99		$\text{V}$
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	4.9			$\text{V}$
		$R_L = 100 \text{ k}\Omega$ to $V_{CM}$	4.996	4.998		$\text{V}$
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	4.985			$\text{V}$
Output Voltage Low	$V_{OL}$	$R_L = 10 \text{ k}\Omega$ to $V_{CM}$		9	30	$\text{mV}$
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			90	$\text{mV}$
		$R_L = 100 \text{ k}\Omega$ to $V_{CM}$		1	4	$\text{mV}$
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			13	$\text{mV}$
Short-Circuit Current	$I_{SC}$	$V_{OUT} = V_{SY}$ or $\text{GND}$		15		$\text{mA}$
Closed-Loop Output Impedance	$Z_{OUT}$	$f = 1 \text{ kHz}$ , $G = 10$		1		$\Omega$
POWER SUPPLY						
Power Supply Rejection Ratio	PSRR	$1.8 \text{ V} \leq V_{SY} \leq 5.5 \text{ V}$	110	135		$\text{dB}$
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	106			$\text{dB}$
Supply Current per Amplifier	$I_{SY}$	$V_{OUT} = V_{SY}/2$		13	17	$\mu\text{A}$
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			20	$\mu\text{A}$
DYNAMIC PERFORMANCE						
Slew Rate	$SR^+$	$R_L = 10 \text{ k}\Omega$ , $C_L = 100 \text{ pF}$ , $G = 1$		0.06		$\text{V}/\mu\text{s}$
	$SR^-$	$R_L = 10 \text{ k}\Omega$ , $C_L = 100 \text{ pF}$ , $G = 1$		0.04		$\text{V}/\mu\text{s}$
Settling Time	$t_s$	To 0.1%, $V_{IN} = 1 \text{ V p-p}$ , $R_L = 10 \text{ k}\Omega$ , $C_L = 100 \text{ pF}$		110		$\mu\text{s}$
Gain Bandwidth Product	GBP	$C_L = 100 \text{ pF}$ , $G = 1$		125		$\text{kHz}$
Phase Margin	$\Phi_M$	$C_L = 100 \text{ pF}$ , $G = 1$		40		Degrees
Channel Separation	CS	$V_{IN} = 4.99 \text{ V}$ , $f = 100 \text{ Hz}$		140		$\text{dB}$
NOISE PERFORMANCE						
Voltage Noise	$e_n \text{ p-p}$	$f = 0.1 \text{ Hz to } 10 \text{ Hz}$		1.96		$\mu\text{V p-p}$
Voltage Noise Density	$e_n$	$f = 1 \text{ kHz}$		95		$\text{nV}/\sqrt{\text{Hz}}$
Current Noise Density	$i_n$	$f = 1 \text{ kHz}$		100		$\text{fA}/\sqrt{\text{Hz}}$

## ELECTRICAL CHARACTERISTICS—1.8 V OPERATION

$V_{SY} = 1.8\text{ V}$ ,  $V_{CM} = V_{SY}/2\text{ V}$ ,  $T_A = 25^\circ\text{C}$ , unless otherwise noted.

Table 3.

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
<b>INPUT CHARACTERISTICS</b>						
Offset Voltage	$V_{OS}$	$0\text{ V} \leq V_{CM} \leq 1.8\text{ V}$		2	15	$\mu\text{V}$
Offset Voltage Drift	$\Delta V_{OS}/\Delta T$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		0.02	0.1	$\mu\text{V}/^\circ\text{C}$
Input Bias Current	$I_B$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		5	50	$\text{pA}$
Input Offset Current	$I_{OS}$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$		10	100	$\text{pA}$
Input Voltage Range		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	0		1.8	$\text{V}$
Common-Mode Rejection Ratio	CMRR	$0\text{ V} \leq V_{CM} \leq 1.8\text{ V}$	105	125		$\text{dB}$
Large-Signal Voltage Gain	$A_{VO}$	$R_L = 10\text{ k}\Omega$ , $0.1\text{ V} \leq V_{OUT} \leq V_{SY} - 0.1\text{ V}$	100	130		$\text{dB}$
Input Resistance	$R_{IN}$	$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	100			$\text{dB}$
Input Capacitance, Differential Mode	$C_{INDM}$			8		$\text{M}\Omega$
Input Capacitance, Common Mode	$C_{INCM}$			2		$\text{pF}$
				5		$\text{pF}$
<b>OUTPUT CHARACTERISTICS</b>						
Output Voltage High	$V_{OH}$	$R_L = 10\text{ k}\Omega$ to $V_{CM}$	1.76	1.796		$\text{V}$
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	1.7			$\text{V}$
		$R_L = 100\text{ k}\Omega$ to $V_{CM}$	1.796	1.799		$\text{V}$
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	1.79			$\text{V}$
Output Voltage Low	$V_{OL}$	$R_L = 10\text{ k}\Omega$ to $V_{CM}$		3	20	$\text{mV}$
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			40	$\text{mV}$
		$R_L = 100\text{ k}\Omega$ to $V_{CM}$		1	3	$\text{mV}$
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			9	$\text{mV}$
Short-Circuit Current	$I_{SC}$	$V_{OUT} = V_{SY}$ or $\text{GND}$		13		$\text{mA}$
Closed-Loop Output Impedance	$Z_{OUT}$	$f = 1\text{ kHz}$ , $G = 10$		1		$\Omega$
<b>POWER SUPPLY</b>						
Power Supply Rejection Ratio	PSRR	$1.8\text{ V} \leq V_{SY} \leq 5.5\text{ V}$	110	135		$\text{dB}$
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$	106			$\text{dB}$
Supply Current per Amplifier	$I_{SY}$	$V_{OUT} = V_{SY}/2$		13	17	$\mu\text{A}$
		$-40^\circ\text{C} \leq T_A \leq +125^\circ\text{C}$			20	$\mu\text{A}$
<b>DYNAMIC PERFORMANCE</b>						
Slew Rate	$SR^+$	$R_L = 10\text{ k}\Omega$ , $C_L = 100\text{ pF}$ , $G = 1$		0.04		$\text{V}/\mu\text{s}$
	$SR^-$	$R_L = 10\text{ k}\Omega$ , $C_L = 100\text{ pF}$ , $G = 1$		0.03		$\text{V}/\mu\text{s}$
Settling Time	$t_s$	To 0.1%, $V_{IN} = 1\text{ V p-p}$ , $R_L = 10\text{ k}\Omega$ , $C_L = 100\text{ pF}$		120		$\mu\text{s}$
Gain Bandwidth Product	GBP	$C_L = 100\text{ pF}$ , $G = 1$		115		$\text{kHz}$
Phase Margin	$\Phi_M$	$C_L = 100\text{ pF}$ , $G = 1$		40		Degrees
Channel Separation	CS	$V_{IN} = 1.7\text{ V}$ , $f = 100\text{ Hz}$		140		$\text{dB}$
<b>NOISE PERFORMANCE</b>						
Voltage Noise	$e_n\text{ p-p}$	$f = 0.1\text{ Hz}$ to $10\text{ Hz}$		1.96		$\mu\text{V p-p}$
Voltage Noise Density	$e_n$	$f = 1\text{ kHz}$		95		$\text{nV}/\sqrt{\text{Hz}}$
Current Noise Density	$i_n$	$f = 1\text{ kHz}$		100		$\text{fA}/\sqrt{\text{Hz}}$

## ABSOLUTE MAXIMUM RATINGS

Table 4.

Parameter	Rating
Supply Voltage	6 V
Input Voltage	$\pm V_{SY} \pm 0.3 \text{ V}$
Input Current <sup>1</sup>	$\pm 10 \text{ mA}$
Differential Input Voltage <sup>2</sup>	$\pm V_{SY}$
Output Short-Circuit Duration to GND	Indefinite
Storage Temperature Range	$-65^{\circ}\text{C}$ to $+150^{\circ}\text{C}$
Operating Temperature Range	$-40^{\circ}\text{C}$ to $+125^{\circ}\text{C}$
Junction Temperature Range	$-65^{\circ}\text{C}$ to $+150^{\circ}\text{C}$
Lead Temperature (Soldering, 60 sec)	$300^{\circ}\text{C}$

<sup>1</sup> The input pins have clamp diodes to the power supply pins. Limit input current to 10 mA or less whenever input signals exceed the power supply rail by 0.3 V.

<sup>2</sup> Inputs are protected against high differential voltages by internal series 1.33 k $\Omega$  resistors and back-to-back diode-connected N-MOSFETs (with a typical  $V_T$  of 0.7 V for  $V_{CM}$  of 0 V).

Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those indicated in the operational section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## THERMAL RESISTANCE

$\theta_{JA}$  is specified with the device soldered on a circuit board with its exposed paddle soldered to a pad (if applicable) on a 4-layer JEDEC standard PC board with zero air flow, unless otherwise specified.

Table 5. Thermal Resistance

Package Type	$\theta_{JA}$	$\theta_{JC}$	Unit
5-Lead SOT23	TBD	TBD	$^{\circ}\text{C}/\text{W}$
5-Lead SC70	TBD	TBD	$^{\circ}\text{C}/\text{W}$

## POWER SEQUENCING

The op amp supplies must be established simultaneously with, or before, any input signals are applied. If this is not possible, the input current must be limited to 10 mA.

## ESD CAUTION



**ESD (electrostatic discharge) sensitive device.** Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.